

MEMS manufacturing capability

With our state-of-the-art cleanroom, we support you from pre-feasibility studies to small and medium series production of MEMS. Our team of experienced and dedicated people ensures you a long-term relationship

We combine rigorous industrial practices with flexibility and innovative spirit

Our capability at a glance

- 700 m² clean room class ISO5
- 150 mm state-of-the-art tools
- Working on Si, SOI, Fused Silica, Glass, SiC, YSZ, and other specialty substrates
- ISO9001:2015 and ISO 14001:2015 certified



Lithography

| Process | Equipment | Comments |
|--|---|---|
| Positive resist coating (manual) | Süss Microtech RCD8 coater / hot plate module | Dedicated to positive resist 0.8 µm to > 50 µm thickness |
| Negative resist coating (manual) | Süss Microtech RCD8 coater / hot plate module | SU8, PI, BCB |
| Positive resist coat and develop cluster | Süss Microtech Gamma60 | Cassette to cassette prime, coat EBR & BSR, bake and develop system |
| HMDS vapor primer | Genesis 2020 | |
| Contact aligner 1:1 | Süss Microtech MA6/BA6 | Front to back side align. Bond aligner capability |
| Contact aligner 1:1 automatic | Süss Microtech MA150E | Fully automatic aligner with front side to back side capability |
| Developing resists | Ramgraber wet bench | Manual bathes. Several SRD systems for rinse and dry |
| Bake ovens | Heraeus UT6060 | Several of them |

Furnace processing and CVD

| Process | Equipment | Comments |
|---|-----------------------------------|---|
| Oxydation wet and dry | Horizontal Tempress TS8604/TS6303 | Several tubes. Tmax: 1150°C. 1 x SiC tube, Tmax: 1250°C |
| LPCVD Polysilicon | Horizontal Tempress TS8604 | Polysilicon doped or undoped. P-doped gas processes |
| LPCVD Silicon nitride | Horizontal Tempress TS6603 | Low stress and stoichiometric Silicon nitride. Deposition on pre-structured substrates as encapsulation possible for some metals (eg. Pt) |
| POCl ₃ deposition | Horizontal Tempress TS8604 | POCl ₃ process |
| LPCVD Ta ₂ O ₅ | Horizontal Tempress TS6303 | |
| Annealing processes | ATV Annealing furnace | |
| Rapid Thermal Annealing | Unitemp RTP-150-EP-HV | High Vacuum Rapid Thermal Process furnace with heating rate up to 150 K/s. Max. temp. 1200°C. N ₂ , forming gas and O ₂ lines |
| PECVD deposition SiO ₂ , Si _x N _y , SiON, a-Si, TEOS | SPTS APM cluster tool | Many recipes silane based, stress and refractive index control, TEOS deposition at temperature < 170°C |
| Atomic layer deposition | Oxford FlexAL | Al ₂ O ₃ , ZnO:Al, Pt. Other materials on request Remote plasma option |
| Molecular Vapor deposition | Applied MST | Organic & Inorganic layers from 1 to 500 nm |
| Parylene deposition | Comelec C25 | Parylène C, others on request |

Metal deposition thin film

| Process | Equipment | Comments |
|---------------------------|--------------------------|---|
| E-beam evaporation system | Leybold Univex 500 | Cr, Au, Al, Cu, Ti, Ni, Ta, Pt, more on demand |
| E-beam evaporation system | EVA760 Alliance concept | See above |
| Sputtering | Oerlikon LLS-EVO | Batch deposition. RF etch and degas. DC and RF sputtering. Co-sputtering and reactive sputtering. Deposition T° up to 300°C. Al, AlSi, Cu, Ti, TiW, Ta, TaN, TiN, Cr, Ag, Al ₂ O ₃ , Mo, Pt, Au, Black Cr. More on demand |
| Sputtering | Oerlikon Clusterline 300 | AlN, ZnO, ... Highly doped AlScN (>10% Sc) |

Dry etching

| Process | Equipment | Comments |
|--|---------------------|---|
| Silicon Deep reactive ion etching (DRIE) | SPTS Rapier cluster | Cassette to cassette cluster tool. Etch depth >600 µm. Verticality <0.1°. Smooth sidewalls. End point detection |
| Silicon and oxide deep reactive ion etching (DRIE) | Adixen AMS200 | Cassette to cassette. End point detection |
| ICP etcher | Corial 210 IL | Oxide, fused silica, SiC, glass etching Metal etching: Al, Cr, Pt, AlN, .. Liner system for each process family to avoid cross-contaminations |
| RIE etcher | Alcatel GIR263 | SiO ₂ , SiN and Si etching in fluorine chemistry |
| Downstream plasma stripper | Muegge STP2020 | SU8 stripping system |
| Resist stripping (Barrel etcher) | Tepla Gigabatch 360 | |
| Resist stripping (Barrel etcher) | Tepla PVA300 | |

Wet etching

| Process | Equipment | Comments |
|----------------------------|------------------------|---|
| Wet etching metals | Ramgraber wet bench | Cr, Al, Cu, Au, Ti, ... |
| Wet etching dielectrics | Ramgraber wet bench | HF, BHF, H ₃ PO ₄ |
| Wet etching silicon | Ramgraber wet bench | KOH, TMAH |
| Cleaning processes | Ramgraber wet bench | RCA1, RCA2, Nanostrip, HNO ₃ , BHF, Piranha, ... |
| HF vapor etching | Idonus systems | SiO ₂ etching for structures release |
| Wet stripping processes | Ramgraber wet bench | Lift-off tool, NMP, Iso-2 |
| Several spin rinser dryers | Ramgraber and semitool | |

Electroplating

| Process | Equipment | Comments |
|-------------|--------------------|---|
| Au plating | CSEM custom design | Au electrodeposition in molds up to > 300 µm |
| NiP plating | CSEM custom design | NiP electrodeposition in molds up to > 300 µm |
| Cu plating | CSEM custom design | Other materials available on request |

Wafer bonding

| Process | Equipment | Comments |
|--|---------------------|---|
| Anodic, adhesive, eutectic and thermo-compression bond | Süss Microtech SB6L | Alignment capability < 5 µm. Au/Au, Cu/Cu, Pt/Pt thermo-compression, other materials on request |
| Anodic, adhesive, eutectic and thermo-compression bond | EVG520is | Dual chamber semi-automated wafer bonder with alignment capability < 5 µm. Heating up to 550°C, vacuum and high pressure options, 60 KN force |

Metrology

| Process | Equipment | Comments |
|--|-------------------------------|----------------------------------|
| Optical microscopes | Zeiss, Nikon, ... | Several of them |
| CD measurement system | Nikon NM40 | |
| Automatic CD meas. system | MicroVu 251 | |
| Step height measurement | KLA-Tencor Alphastep P7 | Extended range up to 1 mm |
| White light interferometer | Wyko | |
| Film thickness measurement | Nanocalc | |
| Ellipsometer | Woolmann Alphas SE | |
| Automatic mapping resistivity measurements | AIT CMT SR2000 4 point prober | Semi-automatic system |
| Stress measurement | Tencor FLX-2320A | |
| Wafer bonding inspection | Idonus WBI 200 | Pre/post bonding alignment check |
| IR microscope | Idonus IRM 150 | |
| Digital microscope | Keyence VAX-1000E | |
| Scanning electron microscopy | FEI Quanta 650 | 150 mm wafers |
| Dual beam FIB/SEM | FEI Scios 2 | |
| FTIR spetrometer | Bruker Vertex 70 | |
| Prober manual | Süss Microtech PM5 | |
| Prober semi-automatic | Süss Microtech PA200 | Thermo-chuck -30°C – +200°C |

Machining

| Process | Equipment | Comments |
|----------------------|-----------------|---|
| Automatic dicing SAW | DISCO DAD3350 | |
| Diamond turning | LT Ultra MMC900 | Surface rectification after electroplating. Thickness control down to the micron |